

**Amplifier, Distributed, 0.1W  
1.0-18.0 GHz**

**MAAMGM0002**

903216 —  
PRELIMINARY INFORMATION

**Features**

- ◆ **0.1 Watt Saturated Output Power Level**
- ◆ **4 dB Typical Noise Figure**
- ◆ **MSAG™ Process**

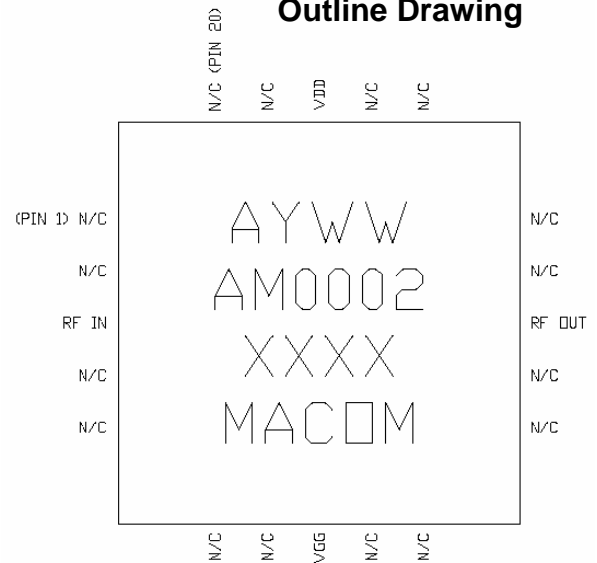
**Description**

The MAAMGM0002 is a 0.1W Distributed Amplifier with on-chip bias networks. This product is fully matched to 50 ohms on both the input and output. The MMIC can be used as a broadband amplifier stage or as a driver stage in high power applications.

Fabricated using M/A-COM's repeatable, high performance and highly reliable GaAs Multifunction Self-Aligned Gate (MSAG™) Process, each device is 100% RF tested on wafer to ensure performance compliance.

M/A-COM's MSAG™ process features robust silicon-like manufacturing processes, planar processing of ion implanted transistors, multiple implant capability enabling power, low-noise, switch and digital FETs on a single chip, and polyimide scratch protection for ease of use with automated manufacturing processes. The use of refractory metals and the absence of platinum in the gate metal formulation prevents hydrogen poisoning when employed in hermetic packaging.

**Outline Drawing**



**Primary Applications**

- ◆ **Test Equipment**
- ◆ **Electronic Warfare**
- ◆ **Radar**

**Maximum Operating Conditions <sup>1</sup>**

Parameter	Symbol	Absolute Maximum	Units
Input Power	P <sub>IN</sub>	18.0	dBm
Drain Supply Voltage	V <sub>DD</sub>	+12.0	V
Gate Supply Voltage	V <sub>GG</sub>	-2.0	V
Quiescent Drain Current (No RF, 60% I <sub>DSS</sub> )	I <sub>DQ</sub>	130	mA
Quiescent DC Power Dissipation (No RF)	P <sub>DISS</sub>	0.9	W
Junction Temperature	T <sub>J</sub>	180	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

**1. Operation outside of these ranges may reduce product reliability. Operation at other than the typical values may result in performance outside the guaranteed limits.**

**Recommended Operating Conditions**

Parameter	Symbol	Min	Typ	Max	Unit
Drain Voltage	V <sub>DD</sub>	4.5	5.0	5.5	V
Gate Voltage	V <sub>GG</sub>	-1.0	-0.6	-0.3	V
Input Power	P <sub>IN</sub>		14	17	dBm
Junction Temperature	T <sub>J</sub>			150	°C
Thermal Resistance	Θ <sub>JC</sub>		91.2		°C/W
Package Base Temperature	T <sub>B</sub>			Note 2	°C

**2. Maximum Package Base Temperature = 150°C — Θ<sub>JC</sub> \* V<sub>DD</sub> \* I<sub>DQ</sub>**

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Visit [www.macom.com](http://www.macom.com) for additional data sheets and product information.

**Electrical Characteristics:**  $T_B = 40^\circ\text{C}^1$ ,  $Z_0 = 50\Omega$ ,  $V_{DD} = 5\text{V}$ ,  $I_{DQ} = 100\text{ mA}$  (~50%  $I_{dss}$ ),  $P_{in} = 14\text{ dBm}$

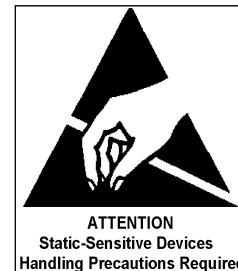
Parameter	Symbol	Typical	Units
Bandwidth	f	1.0 - 18.0	GHz
Output Power	$P_{OUT}$	21	dBm
Power Added Efficiency	PAE	16	%
1-dB Compression Point	P1dB	20	dBm
Small Signal Gain	G	10	dB
Noise Figure	NF	4	dB
Output TOI	OTOI	31	dBm
Input VSWR	VSWR	1.8:1	
Output VSWR	VSWR	1.8:1	
Gate Supply Current	$I_{GG}$	< 2	mA
Drain Supply Current	$I_{DD}$	140	mA

3. Adjust  $V_{GG}$  between -1.0V and -0.3V to achieve  $I_{DQ}$  indicated.

## Operating Instructions

This device is static sensitive. Please handle with care. To operate the device, follow these steps according to which configuration you are using.

1. With  $V_{DD} = 0\text{ V}$ , set  $V_{GG} = -0.8\text{ V}$ .
2. Set  $V_{DD} = 5\text{ V}$ .
3. Adjust  $V_{GG}$  for desired  $I_{DQ}$ .
4. Power down sequence in reverse.
5. Turn off  $V_{GG}$  last.



Typical Performance Curves

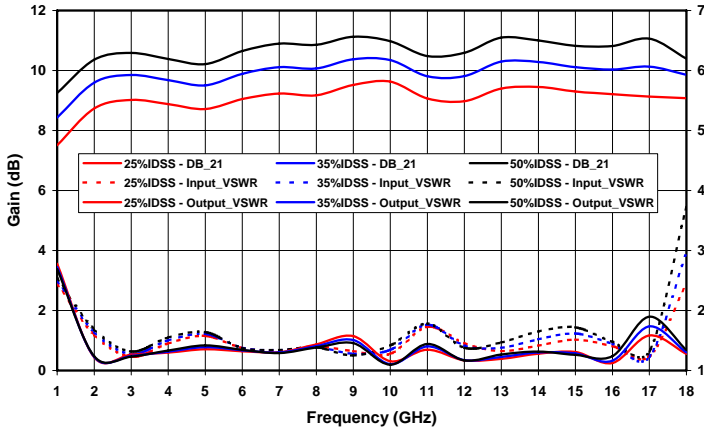


Figure 1. Small Signal Gain, Input and Output VSWR vs. Frequency with  $I_{DQ}$  as a Percentage of  $I_{DSS}$  at  $V_{DS} = 3V$ .

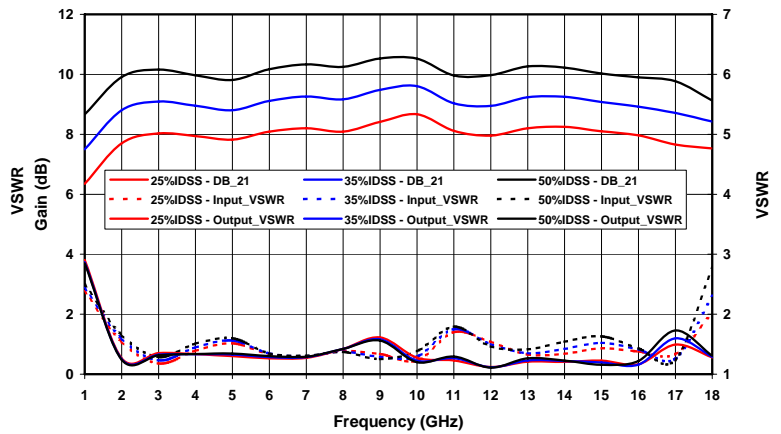


Figure 2. Small Signal Gain, Input and Output VSWR vs. Frequency with  $I_{DQ}$  as a Percentage of  $I_{DSS}$  at  $V_{DS} = 5V$ .

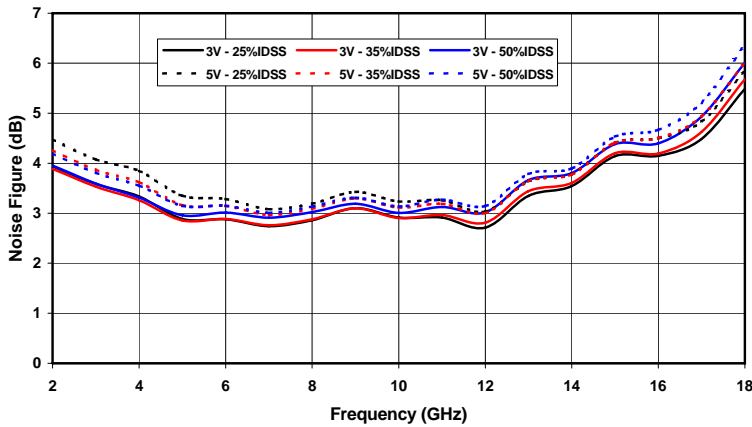


Figure 3. Noise Figure vs. Frequency and  $I_{DQ}$  as a Percentage of  $I_{DSS}$  at  $V_{DS} = 3V$  and  $5V$ .

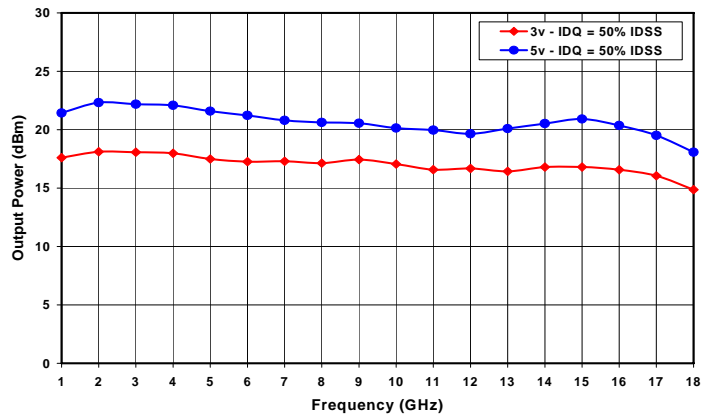


Figure 4. Output Power at 1-dB Compression vs. Frequency



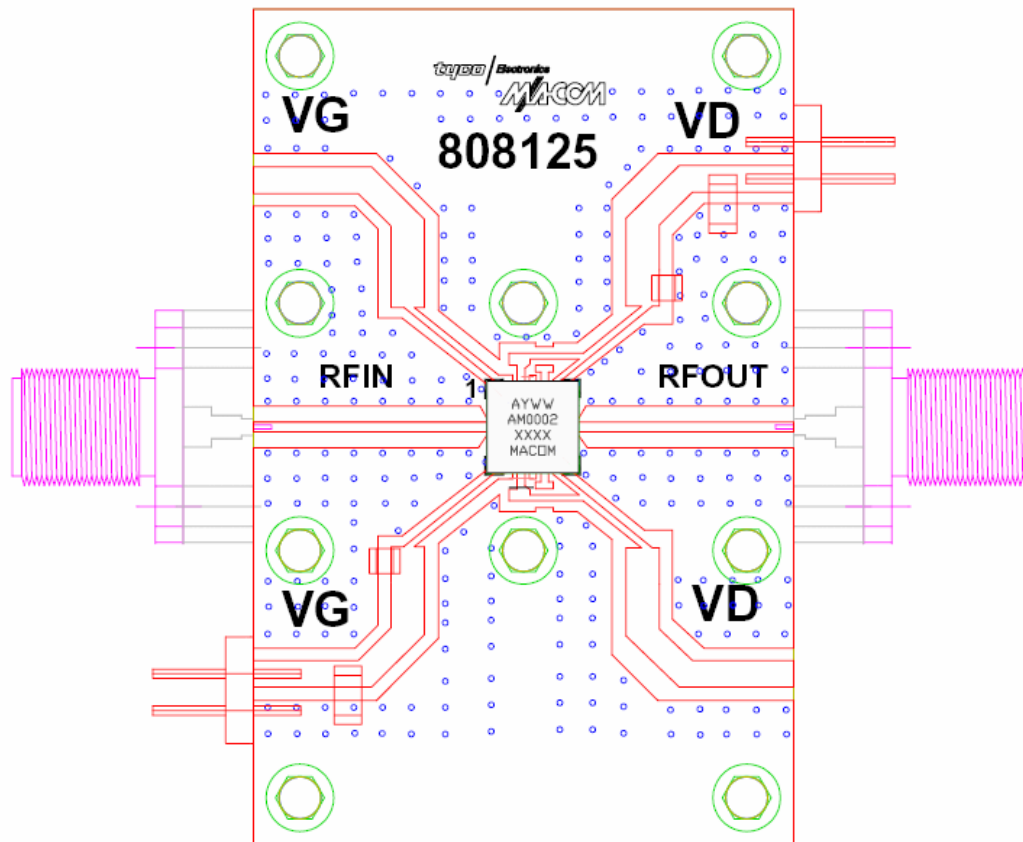


Figure 7. Demonstration Board PN MAAMGM0002-SMB (available upon request).